

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

3LP01SS — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance
- · High-speed switching
- · 2.5V drive

Specifications

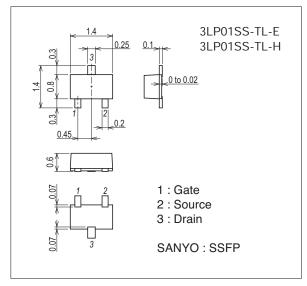
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-0.1	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-0.4	Α
Allowable Power Dissipation	PD		0.15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

Package Dimensions

unit: mm (typ) 7029A-003

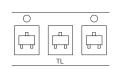


Product & Package Information

• Package : SSFP • JEITA, JEDEC : SC-81

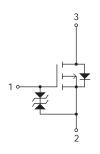
• Minimum Packing Quantity: 8,000 pcs./reel

Packing Type: TL



Marking

Electrical Connection



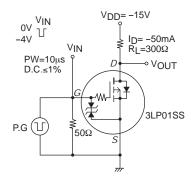
^{*} Machine Model

3LP01SS

Electrical Characteristics at Ta=25°C

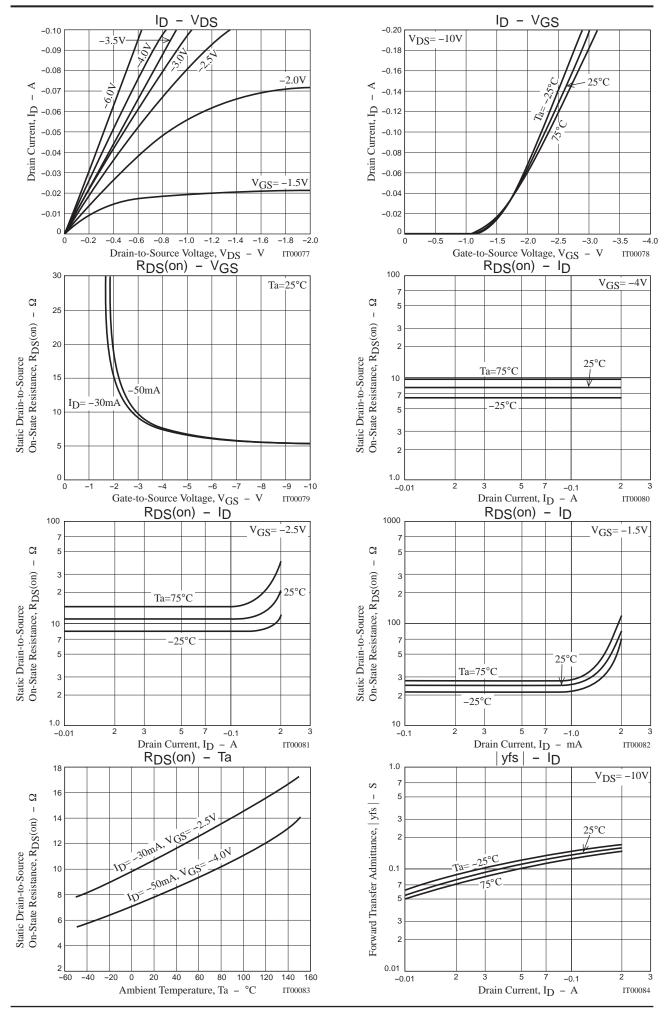
Parameter	Cumbal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID= -1mA, VGS=0V	-30			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} = -30V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} = -10V, I _D = -100μA	-0.4		-1.4	V	
Forward Transfer Admittance	yfs	V _D S= -10V, I _D = -50mA	80	110		mS	
	R _{DS} (on)1	ID= -50mA, VGS= -4V		8	10.4	Ω	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D = -30mA, V _G S= -2.5V		11	15.4	Ω	
	R _{DS} (on)3	I _D = -1mA, V _G S= -1.5V		27	54	Ω	
Input Capacitance	Ciss			7.5		pF	
Output Capacitance	Coss	V _{DS} = -10V, f=1MHz		5.7		pF	
Reverse Transfer Capacitance	Crss			1.8		pF	
Turn-ON Delay Time	t _d (on)			24		ns	
Rise Time	t _r	Considered Took Classifi		55		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		120		ns	
Fall Time	t _f			130		ns	
Total Gate Charge	Qg			1.43		nC	
Gate-to-Source Charge	Qgs	V _{DS} = -10V, V _{GS} = -10V, I _D = -100mA		0.18		nC	
Gate-to-Drain "Miller" Charge	Qgd]		0.25		nC	
Diode Forward Voltage	V _{SD}	I _S = -100mA, V _{GS} =0V		-0.83	-1.2	V	

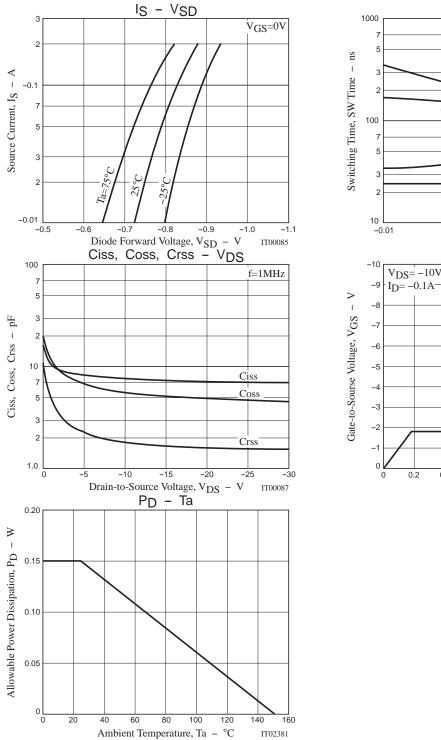
Switching Time Test Circuit

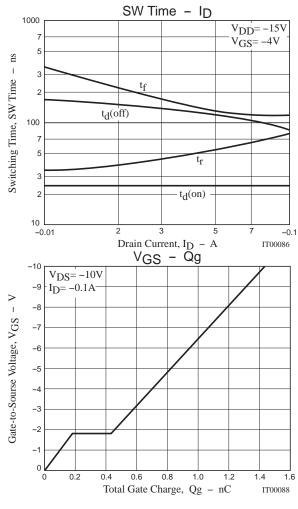


Ordering Information

Device	rice Package Shipping		memo	
3LP01SS-TL-E SSFP		8,000pcs./reel	Pb Free	
3LP01SS-TL-H	SSFP	8,000pcs./reel	Pb Free and Halogen Free	





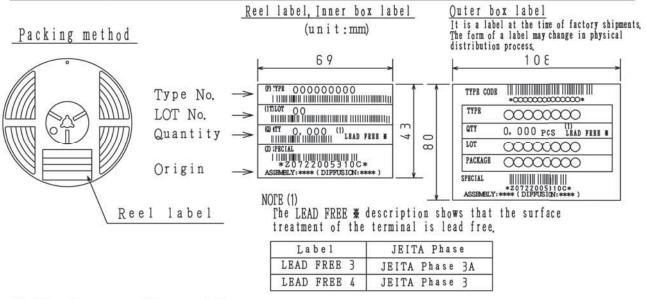


Embossed Taping Specification

3LP01SS-TL-E, 3LP01SS-TL-H

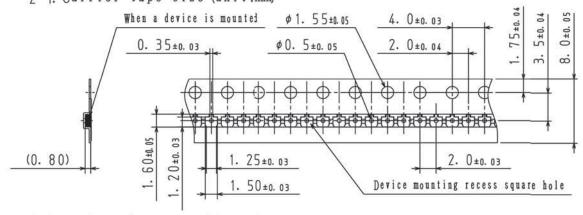
1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)		Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
SSFP	SSFP	8, 000	40, 000	240, 000	5 reels contained Dimensions:mm (external)	6 inner boxes contained Dimension::mm (external)
					183×72×185	440×195×210

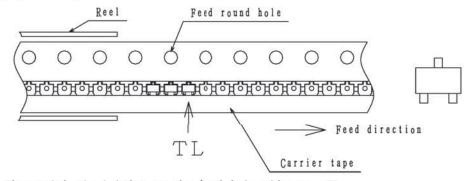


2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

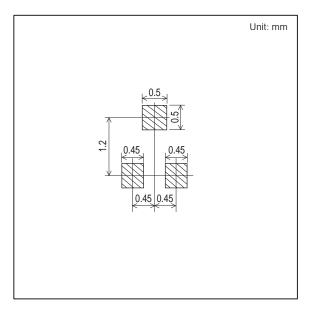


Those with pin 1 index on the feed hole side ·····TL

Outline Drawing

3LP01SS-TL-E, 3LP01SS-TL-H

Land Pattern Example



Note on usage: Since the 3LP01SS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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